

F1 *July 1/2*
79. (Twice Amended) A device according to claim 78 wherein said semiconductor device comprises transistors selected from the group consisting of one of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

F2 *July 1/2*
85. (Twice Amended) A device according to claim 84 wherein said semiconductor device comprises transistors selected from the group consisting of one of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

F3 *July 1/2*
91. (Twice Amended) A device according to claim 90 wherein said semiconductor device comprises transistors selected from the group consisting of one of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

F4 *July 1/2*
97. (Twice Amended) A device according to claim 96 wherein said semiconductor device comprises transistors selected from the group consisting of one of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

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105. (Twice Amended) A device according to claim 102 wherein said semiconductor device comprises transistors selected from the group consisting of one of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

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113. (Twice Amended) A device according to claim 110 wherein said semiconductor device comprises transistors selected from the group consisting of one of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

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121. (Twice Amended) A device according to claim 118 wherein said semiconductor device comprises transistors selected from the group consisting of one of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

F8

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129. (Twice Amended) A device according to claim 126 wherein said semiconductor device comprises transistors selected from the group consisting of one of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

F9

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135. (Twice Amended) A device according to claim 134 wherein said semiconductor device comprises transistors selected from the group consisting of one of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

F10

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141. (Twice Amended) A device according to claim 140 wherein said semiconductor device comprises transistors selected from the group consisting of one of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.